



TSH80-TSH81-TSH82

Wide band rail-to-rail operational amplifier
with standby function

Features

- Operating range from 4.5V to 12V
- 3dB-bandwidth: 100MHz
- Slew-rate 100V/ μ s
- Output current up to 55mA
- Input single supply voltage
- Output rail-to-rail
- Specified for 150 Ω load
- Low distortion, THD 0.1%
- SOT23-5, TSSOP and SO packages

Applications

- Video buffers
- A/D converters driver
- Hi-fi applications

Description

The TSH8x series offers single and dual operational amplifiers featuring high video performance with large bandwidth, low distortion and excellent supply voltage rejection. These amplifiers also feature large output voltage swing and high output current capability to drive standard 150 Ω loads.

Running at single or dual supply voltage from 4.5V to 12V, these amplifiers are tested at 5V (± 2.5 V) and 10V (± 5 V) supplies.

The TSH81 also features a standby mode, which allows the operational amplifier to be put into a standby mode with low power consumption and high output impedance. This function allows power saving or signal switching/multiplexing for high-speed applications and video applications.

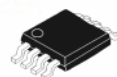
For board space and weight saving, the TSH8x series is proposed in SOT23-5, TSSOP8 and SO-8 plastic micropackages.



SOT23-5

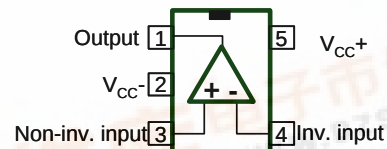


SO-8

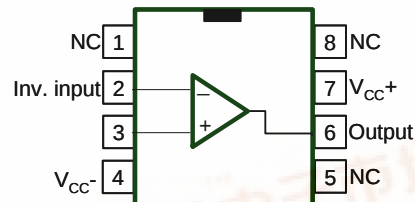


TSSOP8

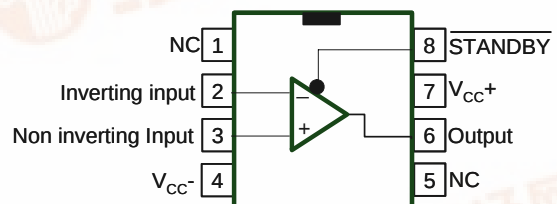
Pin connections TSH80/SOT23-5



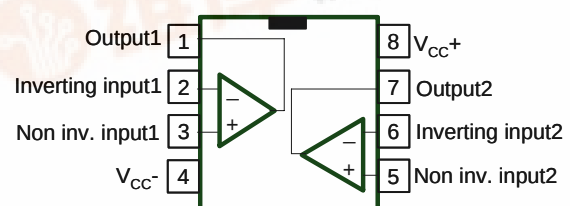
Pin connections TSH80/SO-8



Pin connections TSH81 SO-8/TSSOP8



Pin connections TSH82 SO-8/TSSOP8



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1 Absolute maximum ratings and operating conditions

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{CC}	Supply voltage ⁽¹⁾	14	V
V_{id}	Differential input voltage ⁽²⁾	± 2	V
V_i	Input voltage ⁽³⁾	± 6	V
T_{oper}	Operating free air temperature range	-40 to +85	°C
T_{stg}	Storage temperature	-65 to +150	°C
T_j	Maximum junction temperature	150	°C
R_{thjc}	Thermal resistance junction to case ⁽⁴⁾ SOT23-5 SO8 TSSOP08	80 28 37	°C/W
R_{thja}	Thermal resistance junction to ambient area SOT23-5 SO8 TSSOP08	250 157 130	°C/W
ESD	Human body model (HBM)	2	kV

1. All voltage values, except differential voltage are with respect to network ground terminal.
2. Differential voltages are the non-inverting input terminal with respect to the inverting terminal.
3. The magnitude of input and output must never exceed $V_{CC} + 0.3V$.
4. Short-circuits can cause excessive heating.

Table 2. Operating conditions

Symbol	Parameter	Value	Unit
V_{CC}	Supply voltage	4.5 to 12	V
V_{IC}	Common mode input voltage range	V_{CC}^- to $(V_{CC}^+ - 1.1)$	V
Standby (pin 8)	Threshold on pin 8 for TSH81	(V_{CC}^-) to (V_{CC}^+)	V

2 Electrical characteristics

Table 3. $V_{CC}^+ = +5V$, $V_{CC}^- = GND$, $V_{ic} = 2.5V$, $T_{amb} = 25^\circ C$ (unless otherwise specified)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$ V_{io} $	Input offset voltage	$T_{amb} = 25^\circ C$ $T_{min} < T_{amb} < T_{max}$		1.1	10 12	mV
ΔV_{io}	Input offset voltage drift vs. temperature	$T_{min} < T_{amb} < T_{max}$		3		$\mu V/^\circ C$
I_{io}	Input offset current	$T_{amb} = 25^\circ C$ $T_{min} < T_{amb} < T_{max}$		0.1	3.5 5	μA
I_{ib}	Input bias current	$T_{amb} = 25^\circ C$ $T_{min} < T_{amb} < T_{max}$		6	15 20	μA
C_{in}	Input capacitance			0.3		pF
I_{CC}	Supply current per operator	$T_{amb} = 25^\circ C$ $T_{min} < T_{amb} < T_{max}$		8.2	10.5 11.5	mA
CMR	Common mode rejection ratio ($\delta V_{ic}/\delta V_{io}$)	$+0.1 < V_{ic} < 3.9V$ and $V_{out} = 2.5V$ $T_{amb} = 25^\circ C$ $T_{min} < T_{amb} < T_{max}$	72 70	97		dB
SVR	Supply voltage rejection ratio ($\delta V_{CC}/\delta V_{io}$)	$T_{amb} = 25^\circ C$ $T_{min} < T_{amb} < T_{max}$	68 65	75		dB
PSR	Power supply rejection ratio ($\delta V_{CC}/\delta V_{out}$)	Positive & negative rail		75		dB
A_{vd}	Large signal voltage gain	$R_L = 150\Omega$ connected to 1.5V and $V_{out} = 1V$ to 4V $T_{amb} = 25^\circ C$ $T_{min} < T_{amb} < T_{max}$	75 70	84		dB
I_o	Source	$V_{id} = +1$, V_{out} connected to 1.5V $T_{amb} = 25^\circ C$ $T_{min} < T_{amb} < T_{max}$	35 28	55		mA
	Sink	$V_{id} = -1$, V_{out} connected to 1.5V $T_{amb} = 25^\circ C$ $T_{min} < T_{amb} < T_{max}$	33 28	55		
V_{oh}	High level output voltage	$T_{amb} = 25^\circ C$ $R_L = 150\Omega$ connected to GND $R_L = 600\Omega$ connected to GND $R_L = 2k\Omega$ connected to GND $R_L = 10k\Omega$ connected to GND $R_L = 150\Omega$ connected to 2.5V $R_L = 600\Omega$ connected to 2.5V $R_L = 2k\Omega$ connected to 2.5V $R_L = 10k\Omega$ connected to 2.5V $T_{min} < T_{amb} < T_{max}$ $R_L = 150\Omega$ connected to GND $R_L = 150\Omega$ connected to 2.5V	4.2 4.5 4.1 4.4	4.36 4.85 4.90 4.93 4.66 4.90 4.92 4.93		V

Table 3. $V_{CC}^+ = +5V$, $V_{CC}^- = GND$, $V_{ic} = 2.5V$, $T_{amb} = 25^\circ C$ (unless otherwise specified)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V_{ol}	Low level output voltage	$T_{amb} = 25^\circ C$ $R_L = 150\Omega$ connected to GND $R_L = 600\Omega$ connected to GND $R_L = 2k\Omega$ connected to GND $R_L = 10k\Omega$ connected to GND $R_L = 150\Omega$ connected to 2.5V $R_L = 600\Omega$ connected to 2.5V $R_L = 2k\Omega$ connected to 2.5V $R_L = 10k\Omega$ connected to 2.5V $T_{min} < T_{amb} < T_{max}$ $R_L = 150\Omega$ connected to GND $R_L = 150\Omega$ connected to 2.5V		48 54 55 56 220 105 76 61	150 400 200 450	mV
GBP	Gain bandwidth product	$F = 10MHz$ $A_{VCL} = +11$ $A_{VCL} = -10$		65 55		MHz
Bw	Bandwidth @-3dB	$A_{VCL} = +1$ $R_L = 150\Omega$ connected to 2.5V		87		MHz
SR	Slew rate	$A_{VCL} = +2$ $R_L = 150\Omega // C_L$ to 2.5V $C_L = 5pF$ $C_L = 30pF$	60	104 105		V/ μs
ϕ_m	Phase margin	$R_L = 150\Omega // 30pF$ to 2.5V		40		$^\circ$ (degree)
e_n	Equivalent input noise voltage	$F = 100kHz$		11		nV/ $\sqrt{Hz}$
THD	Total harmonic distortion	$A_{VCL} = +2$, $F = 4MHz$ $R_L = 150\Omega // 30pF$ to 2.5V $V_{out} = 1V_{pp}$ $V_{out} = 2V_{pp}$		-61 -54		dB
IM2	Second order intermodulation product	$A_{VCL} = +2$, $V_{out} = 2V_{pp}$ $R_L = 150\Omega$ connected to 2.5V $F_{in1} = 180kHz$, $F_{in2} = 280kHz$ spurious measurement @100kHz		-76		dBc
IM3	Third order intermodulation product	$A_{VCL} = +2$, $V_{out} = 2V_{pp}$ $R_L = 150\Omega$ to 2.5V $F_{in1} = 180kHz$, $F_{in2} = 280kHz$ spurious measurement @400kHz		-68		dBc
ΔG	Differential gain	$A_{VCL} = +2$, $R_L = 150\Omega$ to 2.5V $F = 4.5MHz$, $V_{out} = 2V_{pp}$		0.5		%
Df	Differential phase	$A_{VCL} = +2$, $R_L = 150\Omega$ to 2.5V $F = 4.5MHz$, $V_{out} = 2V_{pp}$		0.5		$^\circ$ (degree)
Gf	Gain flatness	$F = DC$ to 6MHz, $A_{VCL} = +2$		0.2		dB
Vo1/Vo2	Channel separation	$F = 1MHz$ to 10MHz		65		dB

Table 4. $V_{CC}^+ = +5V$, $V_{CC}^- = -5V$, $V_{ic} = GND$, $T_{amb} = 25^\circ C$ (unless otherwise specified)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$ V_{io} $	Input offset voltage	$T_{amb} = 25^\circ C$ $T_{min} < T_{amb} < T_{max}$		0.8	10 12	mV
ΔV_{io}	Input offset voltage drift vs. temperature	$T_{min} < T_{amb} < T_{max}$		2		$\mu V/^\circ C$
I_{io}	Input offset current	$T_{amb} = 25^\circ C$ $T_{min} < T_{amb} < T_{max}$		0.1	3.5 5	μA
I_{ib}	Input bias current	$T_{amb} = 25^\circ C$ $T_{min} < T_{amb} < T_{max}$		6	15 20	μA
C_{in}	Input capacitance			0.7		pF
I_{CC}	Supply current per operator	$T_{amb} = 25^\circ C$ $T_{min} < T_{amb} < T_{max}$		9.8	12.3 13.4	mA
CMR	Common mode rejection ratio ($\delta V_{ic}/\delta V_{io}$)	$-4.9 < V_{ic} < 3.9V$ and $V_{out}=GND$ $T_{amb} = 25^\circ C$ $T_{min} < T_{amb} < T_{max}$	81 72	106		dB
SVR	Supply voltage rejection ratio ($\delta V_{CC}/\delta V_{io}$)	$T_{amb} = 25^\circ C$ $T_{min} < T_{amb} < T_{max}$	71 65	77		dB
PSR	Power supply rejection ratio ($\delta V_{CC}/\delta V_{out}$)	Positive & negative rail		75		dB
A_{vd}	Large signal voltage gain	$R_L=150\Omega$ connected to GND $V_{out} = -4$ to $+4$ $T_{amb} = 25^\circ C$ $T_{min} < T_{amb} < T_{max}$	75 70	86		dB
I_o	Source	$V_{id}=+1$, V_{out} connected to 1.5V $T_{amb} = 25^\circ C$ $T_{min} < T_{amb} < T_{max}$	35 28	55		mA
	Sink	$V_{id}=-1$, V_{out} connected to 1.5V $T_{amb} = 25^\circ C$ $T_{min} < T_{amb} < T_{max}$	30 28	55		
V_{oh}	High level output voltage	$T_{amb} = 25^\circ C$ $R_L = 150\Omega$ connected to GND $R_L = 600\Omega$ connected to GND $R_L = 2k\Omega$ connected to GND $R_L = 10k\Omega$ connected to GND $T_{min} < T_{amb} < T_{max}$ $R_L = 150\Omega$ connected to GND	4.2 4.1	4.36 4.85 4.9 4.93		V
V_{ol}	Low level output voltage	$T_{amb} = 25^\circ C$ $R_L = 150\Omega$ connected to GND $R_L = 600\Omega$ connected to GND $R_L = 2k\Omega$ connected to GND $R_L = 10k\Omega$ connected to GND $T_{min} < T_{amb} < T_{max}$ $R_L = 150\Omega$ connected to GND		-4.63 -4.86 -4.9 -4.93	-4.4 -4.3	mV

Table 4. $V_{CC}^+ = +5V$, $V_{CC}^- = -5V$, $V_{ic} = GND$, $T_{amb} = 25^\circ C$ (unless otherwise specified)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
GBP	Gain bandwidth product	F=10MHz $A_{VCL} = +11$ $A_{VCL} = -10$		65 55		MHz
Bw	Bandwidth @-3dB	$A_{VCL} = +1$ $R_L = 150\Omega // 30pF$ to GND		100		MHz
SR	Slew rate	$A_{VCL} = +2$ $R_L = 150\Omega // C_L$ to GND $C_L = 5pF$ $C_L = 30pF$	68	117 118		V/ μs
ϕ_m	Phase margin	$R_L = 150\Omega$ connected to GND		40		$^\circ$ (degree)
en	Equivalent input noise voltage	F= 100kHz		11		nV/ $\sqrt{Hz}$
THD	Total harmonic distortion	$A_{VCL} = +2$, F= 4 MHz $R_L = 150\Omega // 30pF$ to GND $V_{out} = 1V_{pp}$ $V_{out} = 2V_{pp}$		-61 -54		dB
IM2	Second order intermodulation product	$A_{VCL} = +2$, $V_{out} = 2V_{pp}$ $R_L = 150\Omega$ to GND $F_{in1} = 180kHz$, $F_{in2} = 280kHz$ spurious measurement @100kHz		-76		dBc
IM3	Third order intermodulation product	$A_{VCL} = +2$, $V_{out} = 2V_{pp}$ $R_L = 150\Omega$ to GND $F_{in1} = 180kHz$, $F_{in2} = 280kHz$ spurious measurement @400kHz		-68		dBc
ΔG	Differential gain	$A_{VCL} = +2$, $R_L = 150\Omega$ to GND F= 4.5MHz, $V_{out} = 2V_{pp}$		0.5		%
Df	Differential phase	$A_{VCL} = +2$, $R_L = 150\Omega$ to GND F= 4.5MHz, $V_{out} = 2V_{pp}$		0.5		$^\circ$ (degree)
Gf	Gain flatness	F=DC to 6MHz, $A_{VCL} = +2$		0.2		dB
Vo1/Vo2	Channel separation	F=1MHz to 10MHz		65		dB

Table 5. Standby mode - V_{CC}^+ , V_{CC}^- , $T_{amb} = 25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V_{low}	Standby low level		V_{CC}^-		$(V_{CC}^- + 0.8)$	V
V_{high}	Standby high level		$(V_{CC}^- + 2)$		(V_{CC}^+)	V
$I_{CC-STBY}$	Current consumption per operator when Standby is active	pin 8 (TSH81) to V_{CC}^-		20	55	μA
Z_{out}	Output impedance ($R_{out} // C_{out}$)	R_{out} C_{out}		10 17		$\text{M}\Omega$ pF
T_{on}	Time from Standby mode to Active mode			2		μs
T_{off}	Time from Active mode to Standby mode	Down to $I_{CC-STBY} = 10\mu\text{A}$		10		μs

Table 6. TSH81 standby control pin status

TSH81 standby control pin 8 ($\overline{\text{STANDBY}}$)	Operator status
V_{low}	Standby
V_{high}	Active

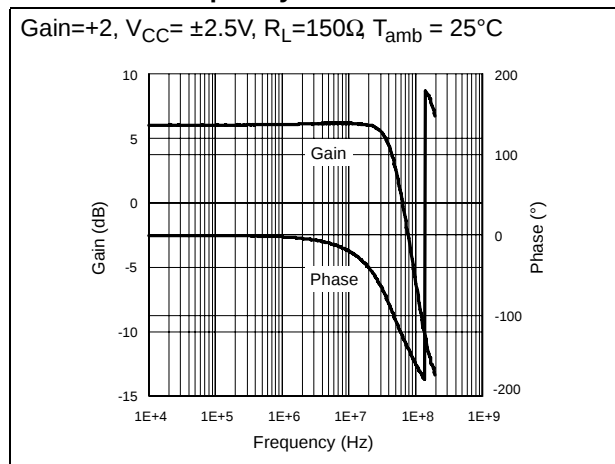
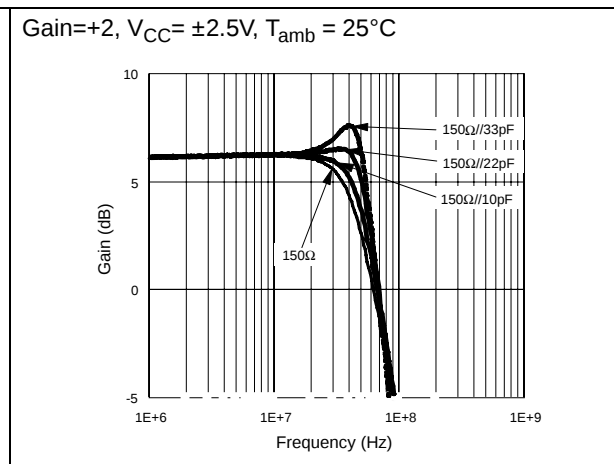
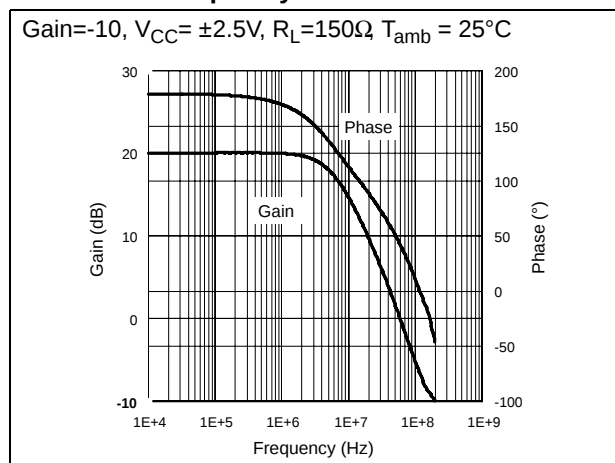
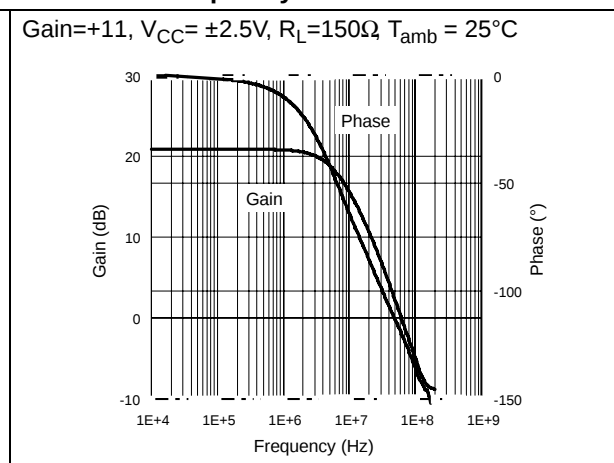
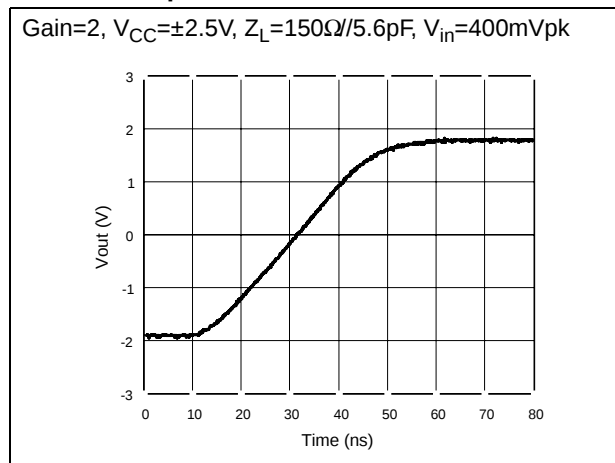
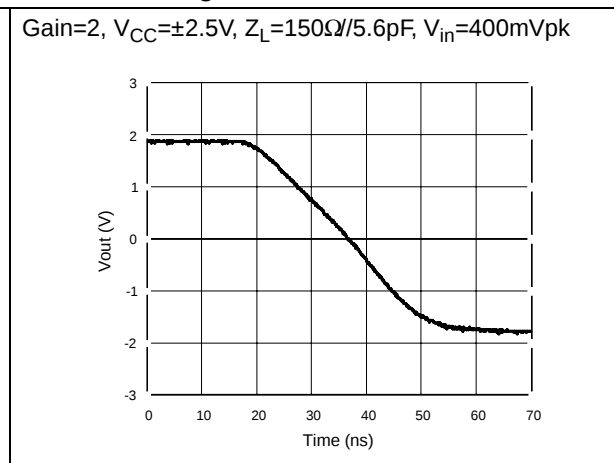
Figure 1. Closed loop gain and phase vs. frequency**Figure 2. Overshoot vs. output capacitance****Figure 3. Closed loop gain and phase vs. frequency****Figure 4. Closed loop gain and phase vs. frequency****Figure 5. Large signal measurement - positive slew rate****Figure 6. Large signal measurement - negative slew rate**

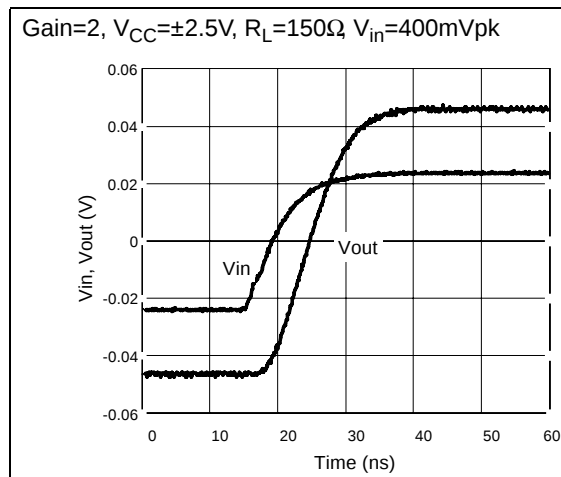
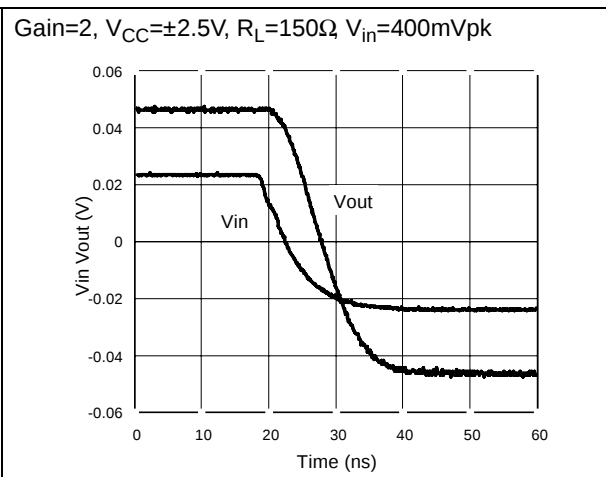
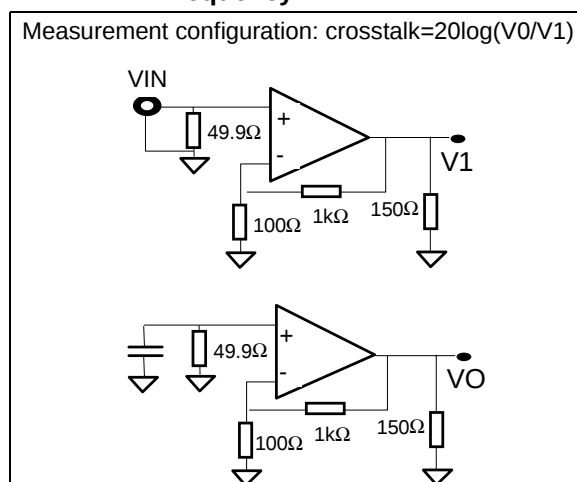
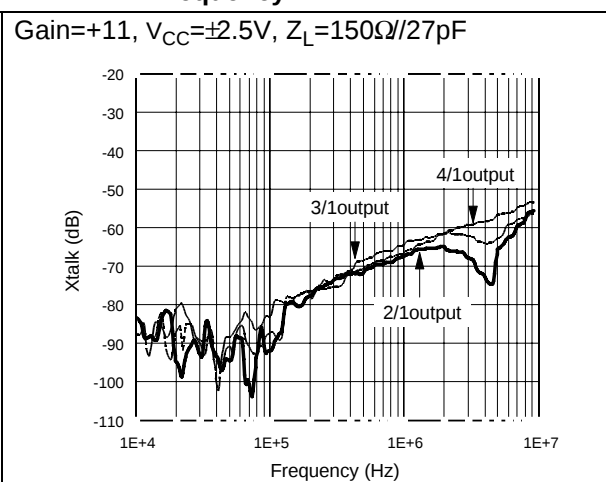
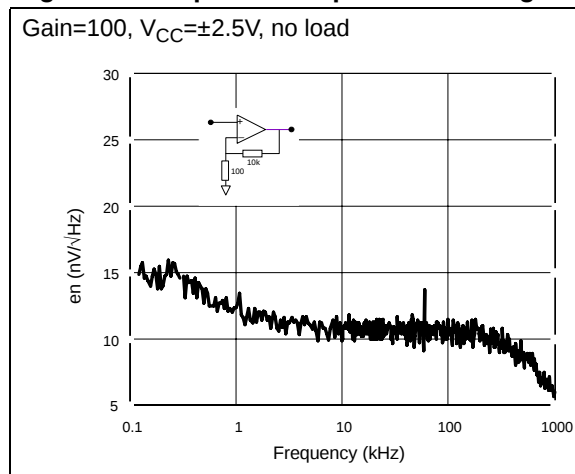
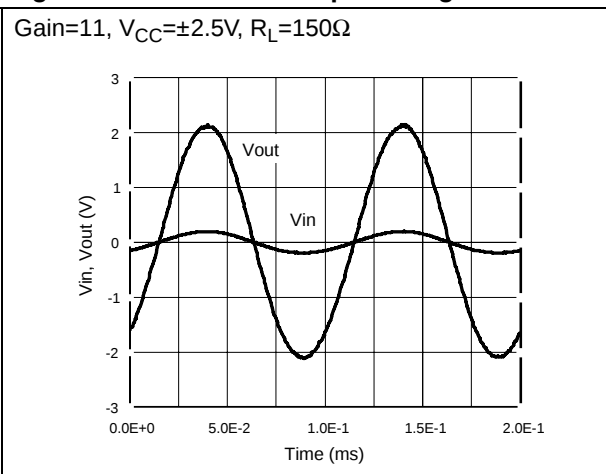
Figure 7. Small signal measurement - rise time**Figure 8. Small signal measurement - fall time****Figure 9. Channel separation (crosstalk) vs. frequency****Figure 10. Channel separation (crosstalk) vs. frequency****Figure 11. Equivalent input noise voltage****Figure 12. Maximum output swing**

Figure 13. Standby mode - T_{on} , T_{off}

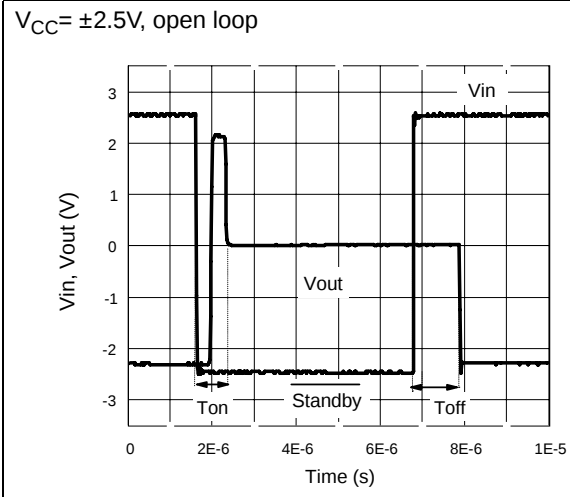
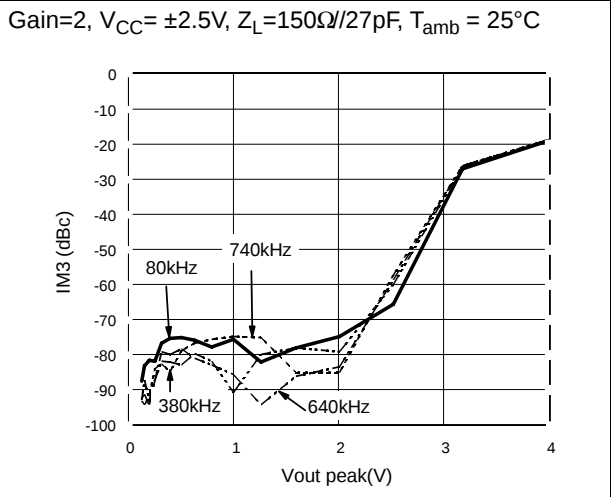


Figure 14. Third order intermodulation⁽¹⁾



1. The IFR2026 synthesizer generates a two-tone signal ($F_1=180kHz$, $F_2=280kHz$), each tone having the same amplitude. The HP3585 spectrum analyzer measures the intermodulation products as a function of the output voltage. The generator and the spectrum analyzer are phase locked for better accuracy.

Figure 15. Group delay

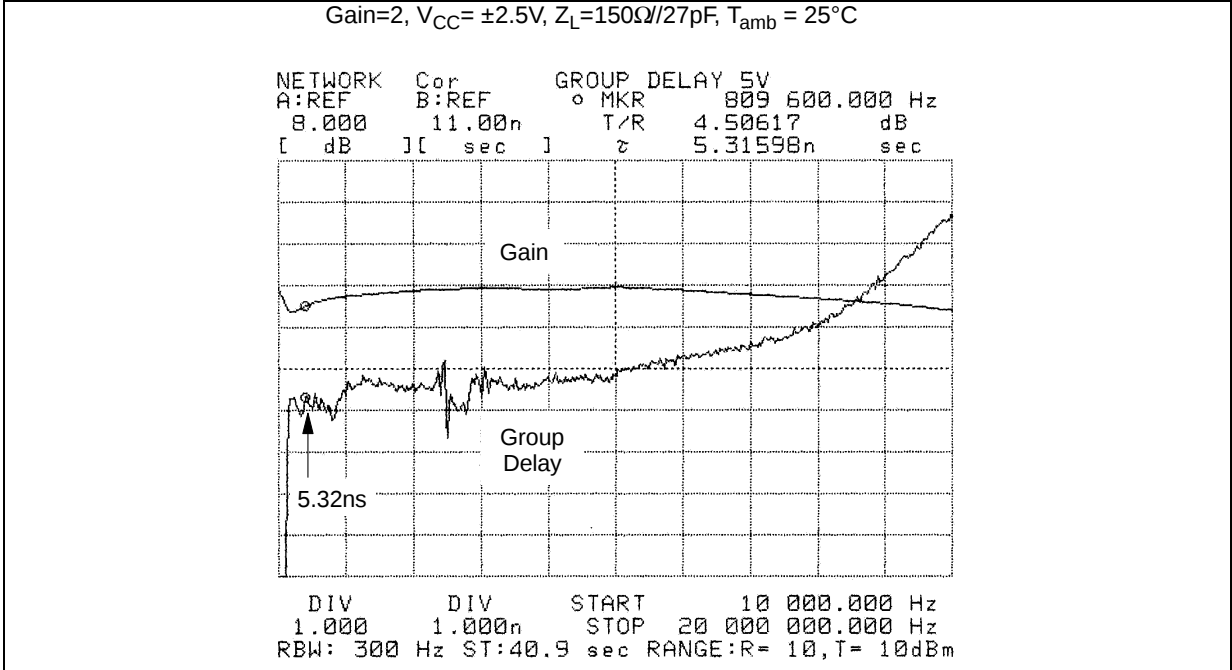


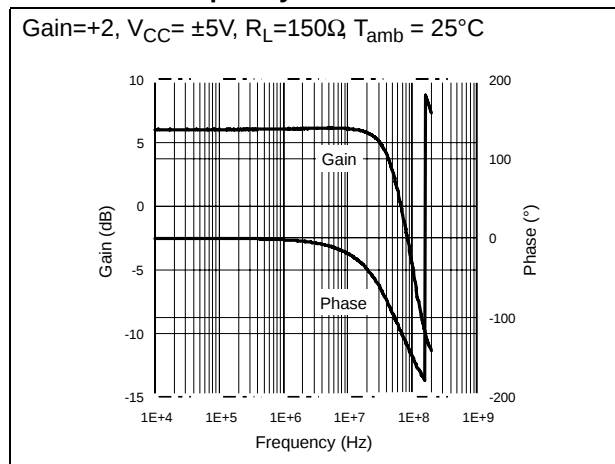
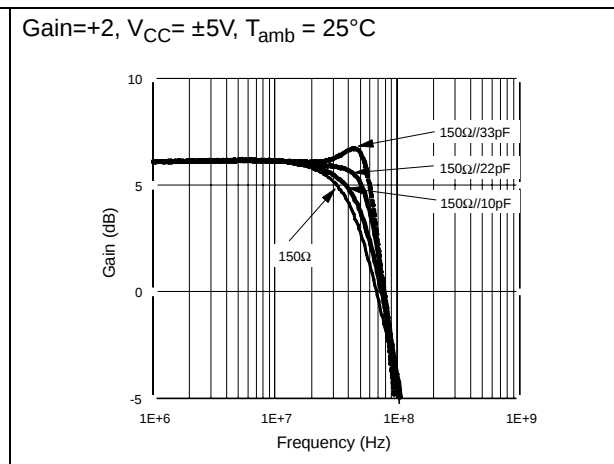
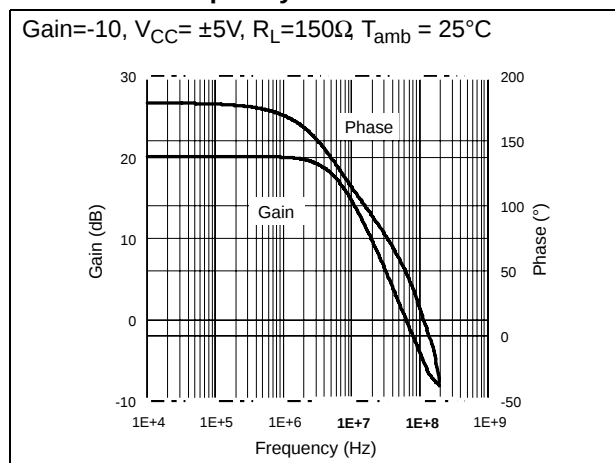
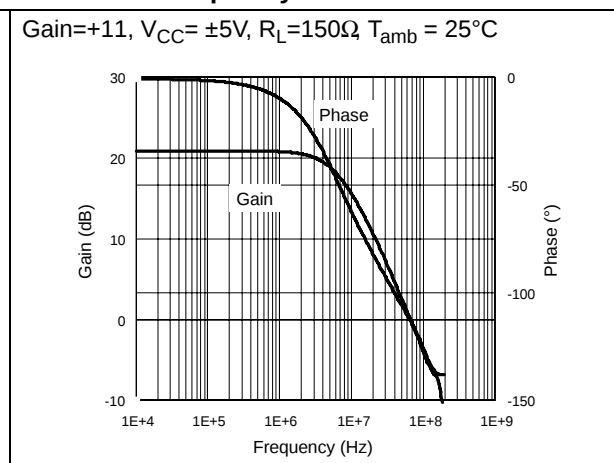
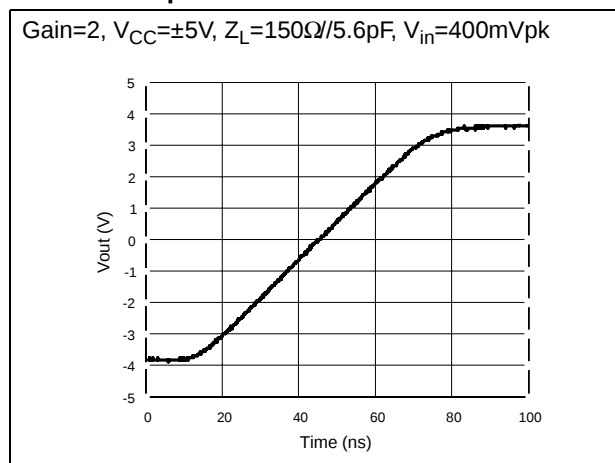
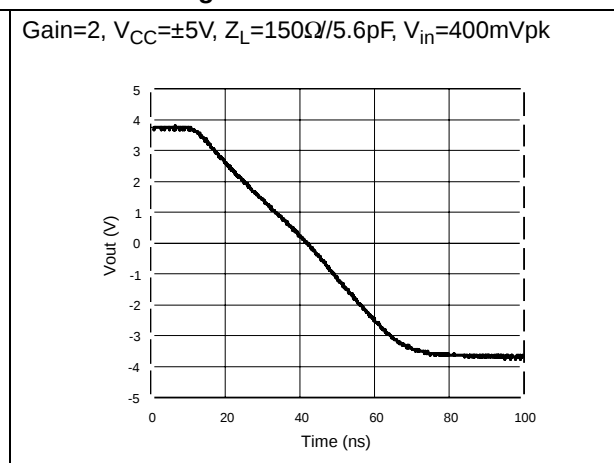
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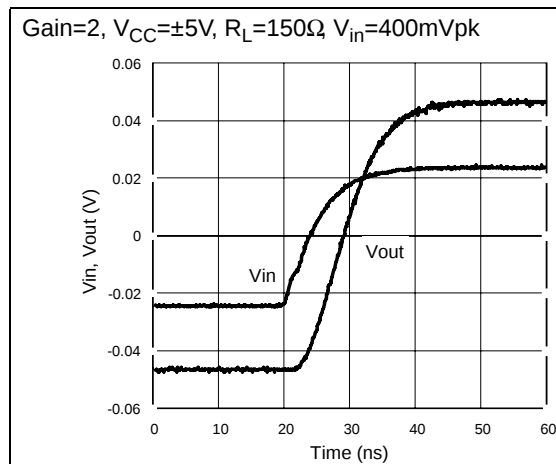
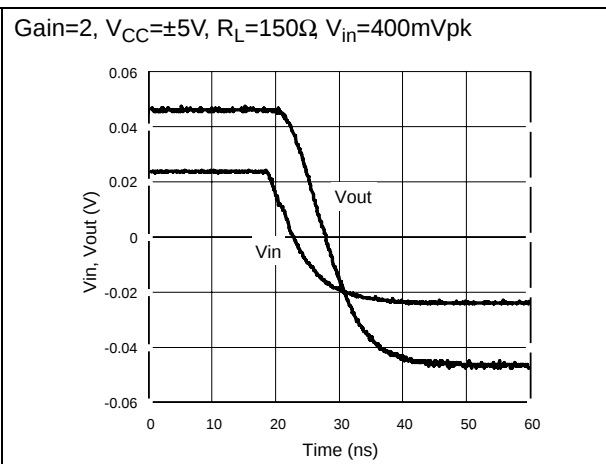
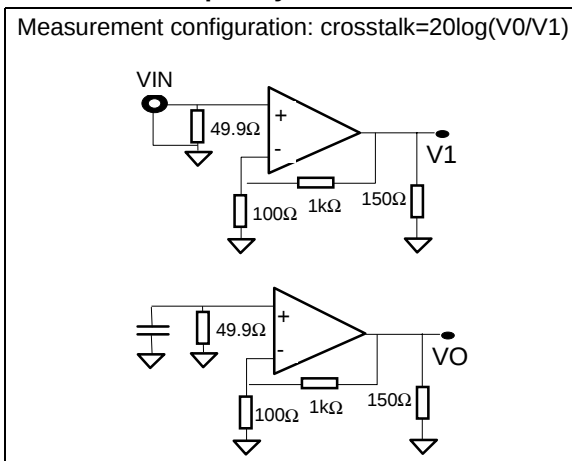
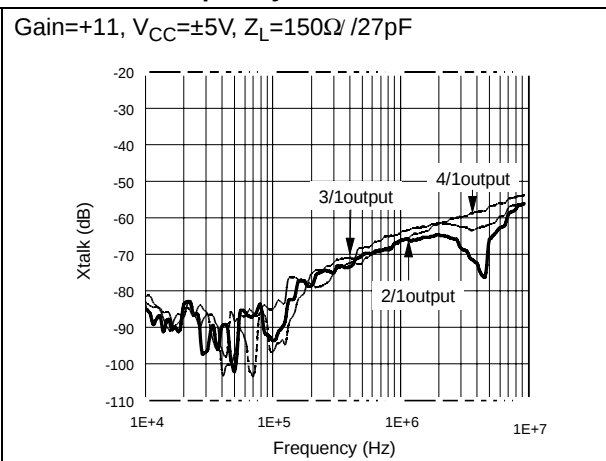
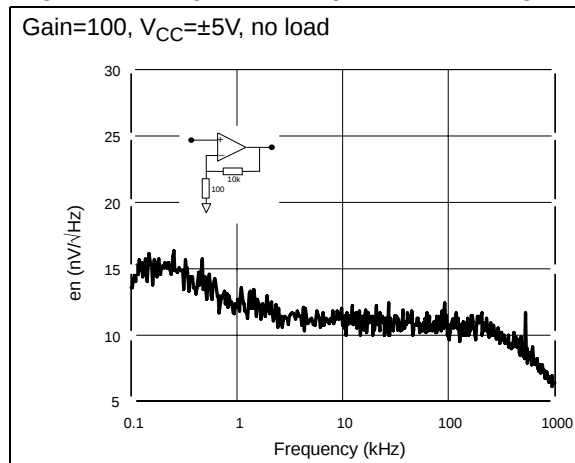
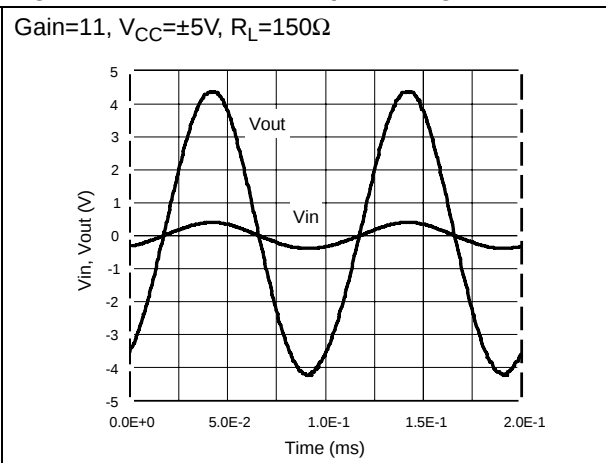
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Figure 28. Standby mode - T_{on} , T_{off}

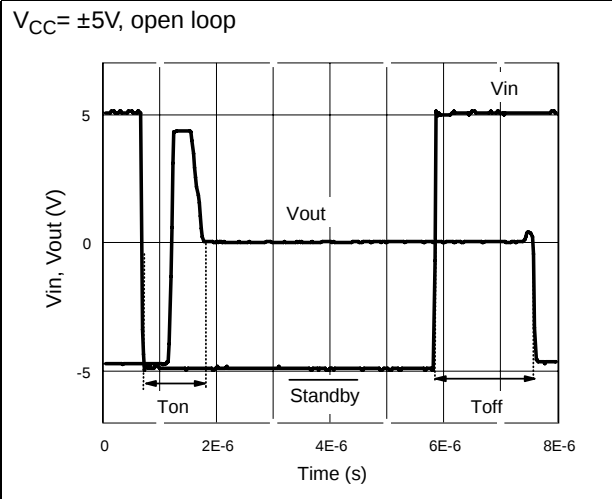
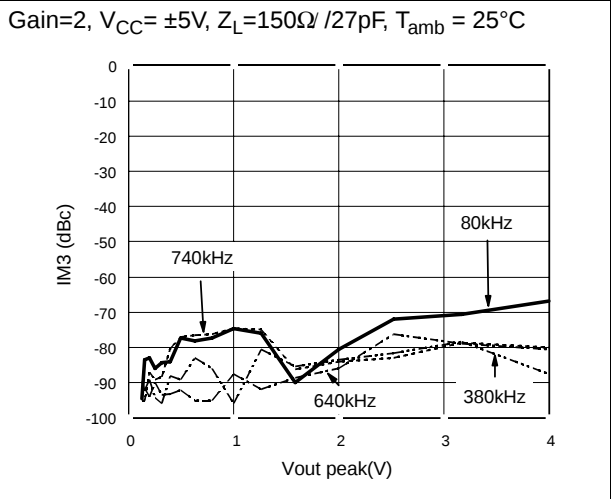
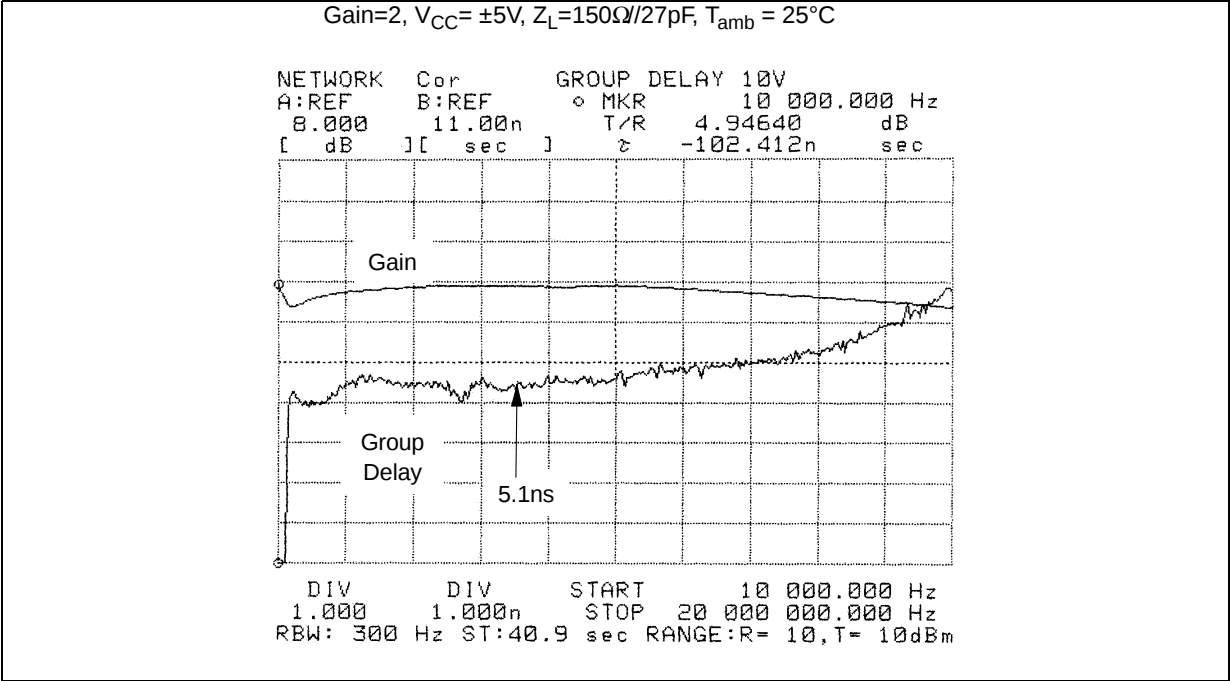


Figure 29. Third order intermodulation⁽¹⁾



1. The IFR2026 synthesizer generates a two-tone signal ($F_1=180kHz$, $F_2=280kHz$), each tone having the same amplitude. The HP3585 spectrum analyzer measures the intermodulation products as a function of the output voltage. The generator and the spectrum analyzer are phase locked for better accuracy.

Figure 30. Group delay



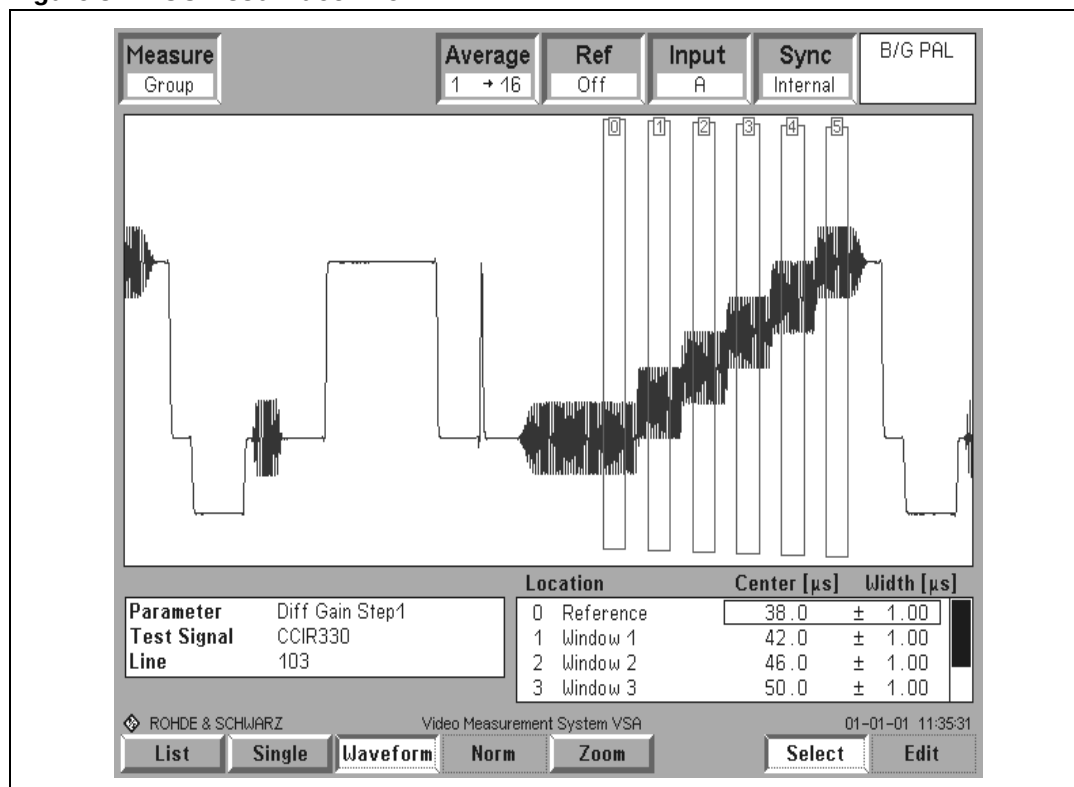
3 Test conditions

3.1 Layout precautions

To use the TSH8X circuits in the best manner at high frequencies, some precautions have to be taken for power supplies:

- In high-speed circuit applications, the implementation of a proper ground plane on both sides of the PCB is mandatory to ensure low inductance and low resistance common return.
- Power supply bypass capacitors (4.7 μ F and ceramic 100pF) should be placed as close as possible to the IC pins in order to improve high frequency bypassing and reduce harmonic distortion. The power supply capacitors must be incorporated for both the negative and the positive pins.
- All inputs and outputs must be properly terminated with output resistors; thus, the amplifier load is resistive only and the stability of the amplifier will be improved.
All leads must be wide and as short as possible especially for op-amp inputs and outputs in order to decrease parasitic capacitance and inductance.
- In lower gain applications, use a low feedback resistance (under 1k Ω) to reduce the time constant with parasitic capacitance.
- Choose component sizes as small as possible (SMD).
- On the output, the load capacitance must be negligible to maintain good stability. You can put a serial resistance as close as possible to the output pin to minimize the effect of the load capacitance.

Figure 31. CCIR330 video line



3.2 Video capabilities

To characterize the differential phase and differential gain a CCIR330 video line is used.

The video line contains 5 (flat) levels of luminance onto which the chrominance signal is superimposed. The luminance gives various amplitudes which define the saturation of the signal. The chrominance gives various phases which define the color of the signal.

Differential phase (or differential gain) distortion is present if a signal chrominance phase (gain) is affected by luminance level. Differential phase and gain represent the ability to uniformly process the high frequency information at all luminance levels.

When differential gain is present, color saturation is not correctly reproduced.

The input generator is the Rhode & Schwarz CCVS. The output measurement is done by the Rhode and Schwarz VSA.

Figure 32. Measurement on Rhode and Schwarz VSA

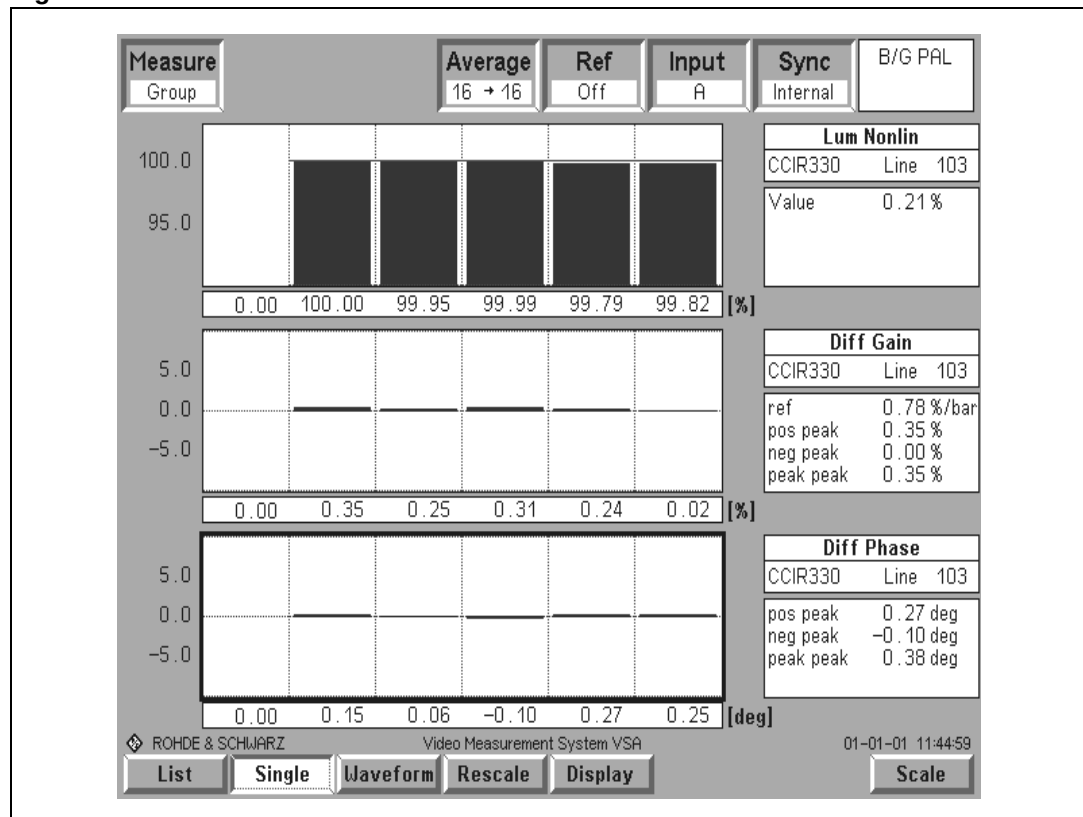


Table 7. Video results

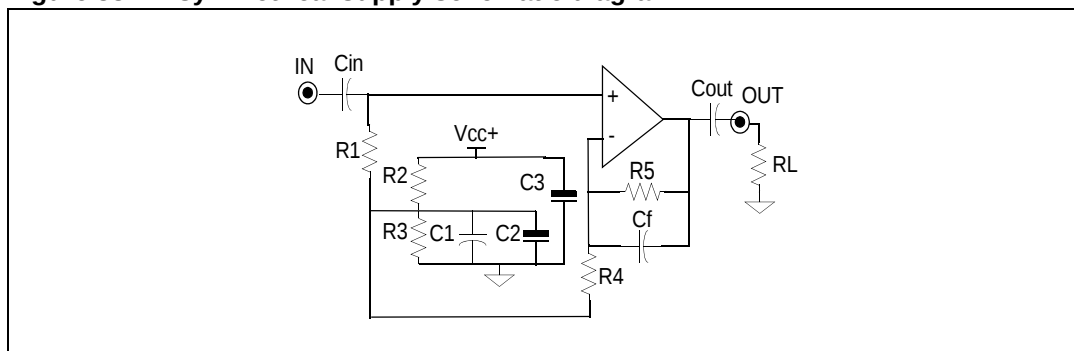
Parameter	Value ($V_{CC}=\pm 2.5V$)	Value ($V_{CC}=\pm 5V$)	Unit
Lum NL	0.1	0.3	%
Lum NL Step 1	100	100	%
Lum NL Step 2	100	99.9	%
Lum NL Step 3	99.9	99.8	%
Lum NL Step 4	99.9	99.9	%
Lum NL Step 5	99.9	99.7	%
Diff Gain pos	0	0	%
Diff Gain neg	-0.7	-0.6	%
Diff Gain pp	0.7	0.6	%
Diff Gain Step1	-0.5	-0.3	%
Diff Gain Step2	-0.7	-0.6	%
Diff Gain Step3	-0.3	-0.5	%
Diff Gain Step4	-0.1	-0.3	%
Diff Gain Step5	-0.4	-0.5	%
Diff Phase pos	0	0.1	degree
Diff Phase neg	-0.2	-0.4	degree
Diff Phase pp	0.2	0.5	degree
Diff Phase Step1	-0.2	-0.4	degree
Diff Phase Step2	-0.1	-0.4	degree
Diff Phase Step3	-0.1	-0.3	degree
Diff Phase Step4	0	0.1	degree
Diff Phase Step5	-0.2	-0.1	degree

4 Precautions on asymmetrical supply operation

The TSH8x can be used either with a dual or a single supply. If a single supply is used, the inputs are biased to the mid-supply voltage ($+V_{CC}/2$). This bias network must be carefully designed, in order to reject any noise present on the supply rail.

As the bias current is $15\mu A$, you should use a high resistance $R1$ (approximately $10k\Omega$) to avoid introducing an offset mismatch at the amplifier inputs.

Figure 33. Asymmetrical supply schematic diagram



$C1$, $C2$, $C3$ are bypass capacitors intended to filter perturbation from V_{CC} . The following capacitor values are appropriate:

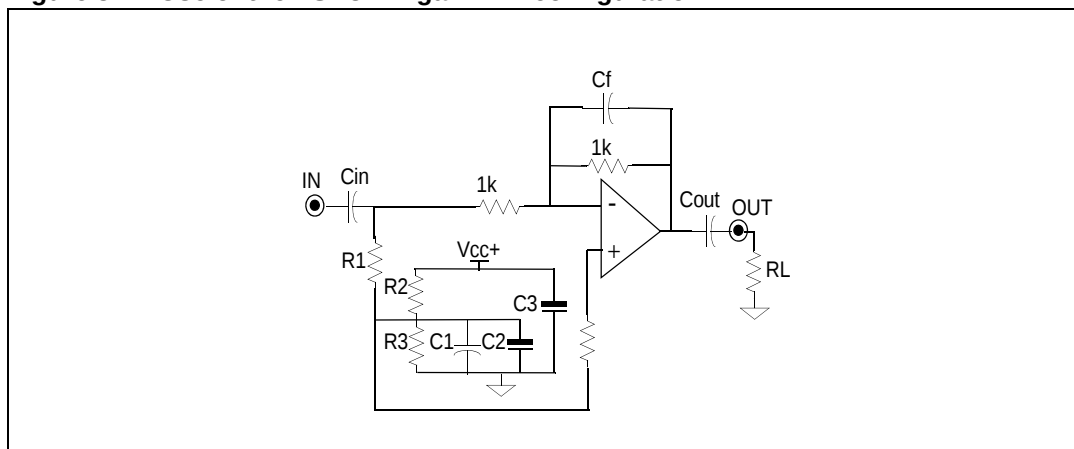
$$C1=100nF \text{ and } C2=C3=100\mu F$$

$R2$ and $R3$ are such that the current through them must be superior to 100 times the bias current. Therefore, you could use the following resistance values:

$$R2=R3=4.7k\Omega$$

C_{in} and C_{out} are chosen to filter the DC signal by the low pass filters ($R1$, C_{in}) and (R_{out} , C_{out}). With $R1=10k\Omega$, $R_{out}=R_L=150\Omega$, and $C_{in}=2\mu F$, $C_{out}=220\mu F$ the cutoff frequency obtained is lower than 10Hz.

Figure 34. Use of the TSH8x in gain = -1 configuration



5 Package information

In order to meet environmental requirements, STMicroelectronics offers these devices in ECOPACK® packages. These packages have a lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an STMicroelectronics trademark. ECOPACK specifications are available at: www.st.com.

5.1 SO-8 package mechanical data

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A			1.75			0.069
A1	0.10		0.25	0.004		0.010
A2	1.25			0.049		
b	0.28		0.48	0.011		0.019
c	0.17		0.23	0.007		0.010
D	4.80	4.90	5.00	0.189	0.193	0.197
H	5.80	6.00	6.20	0.228	0.236	0.244
E1	3.80	3.90	4.00	0.150	0.154	0.157
e		1.27			0.050	
h	0.25		0.50	0.010		0.020
L	0.40		1.27	0.016		0.050
k	1°		8°	1°		8°
ccc			0.10			0.004

5.2 TSSOP8 package mechanical data

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A			1.2			0.047
A1	0.05		0.15	0.002		0.006
A2	0.80	1.00	1.05	0.031	0.039	0.041
b	0.19		0.30	0.007		0.012
c	0.09		0.20	0.004		0.008
D	2.90	3.00	3.10	0.114	0.118	0.122
E	6.20	6.40	6.60	0.244	0.252	0.260
E1	4.30	4.40	4.50	0.169	0.173	0.177
e		0.65			0.0256	
k	0°		8°	0°		8°
L	0.45	0.60	0.75	0.018	0.024	0.030
L1		1			0.039	
aaa		0.1			0.004	

5.3 SOT23-5 package mechanical data

Ref.	Dimensions					
	Millimeters			Mils		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	0.90		1.45	35.4		57.1
A1	0.00		0.15	0.00		5.9
A2	0.90		1.30	35.4		51.2
b	0.35		0.50	13.7		19.7
C	0.09		0.20	3.5		7.8
D	2.80		3.00	110.2		118.1
E	2.60		3.00	102.3		118.1
E1	1.50		1.75	59.0		68.8
e		0.95			37.4	
e1		1.9			74.8	
L	0.35		0.55	13.7		21.6

The diagram illustrates the mechanical dimensions of the SOT23-5 package. The left view is a side profile showing dimensions A (total width), A1 (lead thickness), A2 (lead width), b (lead thickness), C (lead angle), and L (lead length). The right view is a top-down perspective showing dimensions D (package width), E (package height), E1 (package body height), e (pitch), e1 (pitch), and b (lead thickness).

6 Ordering information

Table 8. Order codes

Type	Temperature range	Package	Packaging	Marking
TSH80ILT	-40°C to +85°C	SOT23-5	Tape & reel	K303
TSH80IYLT ⁽¹⁾		SOT23-5 (Automotive grade level)		K310
TSH80ID/DT		SO-8	Tube or tape & reel	TSH80I
TSH80IYD/IYDT ⁽¹⁾		SO-8 (Automotive grade level)		SH80IY
TSH81ID/DT		SO-8		TSH81I
TSH81IPT		TSSOP8	Tape & reel	SH81I
TSH81IYPT ⁽¹⁾		TSSOP8 (Automotive grade level)		H81IY
TSH82ID/DT		SO-8	Tube or tape & reel	TSH82I
TSH82IPT		TSSOP8	Tape & reel	SH82I
TSH82IYD/IYDT ⁽¹⁾		SO-8 (Automotive grade level)	Tube or tape & reel	SH82IY

1. Qualification and characterization according to AEC Q100 and Q003 or equivalent, advanced screening according to AEC Q001 & Q 002 or equivalent are on-going.

7 Revision history

Date	Revision	Changes
1-Feb-2003	1	First release.
2-Aug-2005	2	PPAP references inserted in the datasheet, see Table 8: Order codes on page 23 .
12-Apr-2007	3	Corrected temperature range for TSH80IYD/IYDT and TSH82IYD/IYDT order codes in Table 8: Order codes on page 23 .
24-Oct-2007	4	TSH81IYPT PPAP references inserted in the datasheet, see Table 8: Order codes on page 23 .

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